

V_{DSS}	-20V
$R_{DS(on)}$ (Max.)	3.8Ω
I_D	-100mA
P_D	150mW

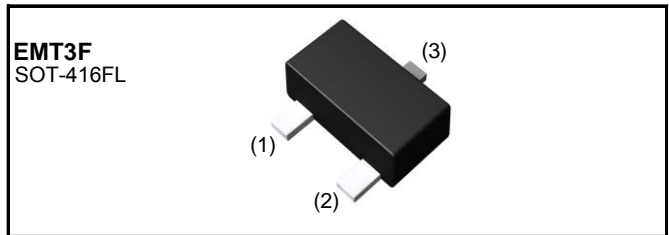
●Features

- 1) Low voltage drive(1.2V) makes this device ideal for portable equipment.
- 2) Drive circuits can be simple.
- 3) Built-in G-S Protection Diode.

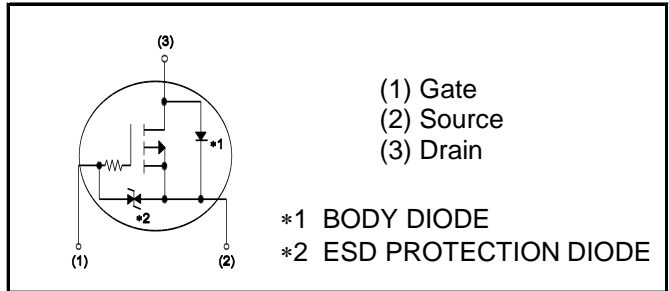
●Application

Switching

●Outline



●Inner circuit



●Packaging specifications

Type	Packaging	Taping
	Reel size (mm)	180
	Tape width (mm)	8
	Basic ordering unit (pcs)	3,000
	Taping code	TL
	Marking	RX

●Absolute maximum ratings($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Drain - Source voltage	V_{DSS}	-20	V
Continuous drain current	I_D^{*1}	±100	mA
Pulsed drain current	$I_{D,pulse}^{*2}$	±400	mA
Gate - Source voltage	V_{GSS}	±10	V
Power dissipation	P_D^{*3}	150	mW
Junction temperature	T_j	150	°C
Range of storage temperature	T_{stg}	-55 to +150	°C

●Thermal resistance

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Thermal resistance, junction - ambient	R_{thJA}^{*3}	-	-	833	°C/W

●Electrical characteristics($T_a = 25^\circ\text{C}$) ,unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -1mA$	-20	-	-	V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = -20V, V_{GS} = 0V$	-	-	-1	μA
Gate - Source leakage current	I_{GSS}	$V_{GS} = \pm 10V, V_{DS} = 0V$	-	-	± 10	μA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = -10V, I_D = -100\mu\text{A}$	-0.3	-	-1.0	V
Static drain - source on - state resistance	$R_{DS(on)}$ *4	$V_{GS} = -4.5V, I_D = -100mA$	-	2.5	3.8	Ω
		$V_{GS} = -2.5V, I_D = -50mA$	-	3.4	5.1	
		$V_{GS} = -1.8V, I_D = -20mA$	-	4.8	8.2	
		$V_{GS} = -1.5V, I_D = -10mA$	-	6.0	13.2	
		$V_{GS} = -1.2V, I_D = -1mA$	-	10.0	40.0	
		$V_{GS} = -4.5V, I_D = -100mA, T_j = 125^\circ\text{C}$	-	4.8	6.8	
Transconductance	g_{fs} *4	$V_{DS} = -10V, I_D = -100mA$	120	-	-	mS

*1 Limited only by maximum temperature allowed.

*2 $P_w \leq 10\mu\text{s}$, Duty cycle $\leq 1\%$

*3 Each terminal mounted on a recommended land

*4 Pulsed

●Electrical characteristics($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Input capacitance	C_{iss}	$V_{GS} = 0V$	-	15	-	pF
Output capacitance	C_{oss}	$V_{DS} = -10V$	-	4.0	-	
Reverse transfer capacitance	C_{rss}	$f = 1\text{MHz}$	-	1.5	-	
Turn - on delay time	$t_{d(on)}^{*4}$	$V_{DD} \approx -10V, V_{GS} = -4.5V$	-	46	-	ns
Rise time	t_r^{*4}	$I_D = -50\text{mA}$	-	62	-	
Turn - off delay time	$t_{d(off)}^{*4}$	$R_L = 200\Omega$	-	325	-	
Fall time	t_f^{*4}	$R_G = 10\Omega$	-	137	-	

●Body diode electrical characteristics (Source-Drain)($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Continuous source current	I_s^{*1}	$T_c = 25^\circ\text{C}$	-	-	-100	mA
Pulsed source current	I_{SM}^{*2}		-	-	-400	mA
Forward voltage	V_{SD}^{*4}	$V_{GS} = 0V, I_s = -100\text{mA}$	-	-	-1.2	V

●Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

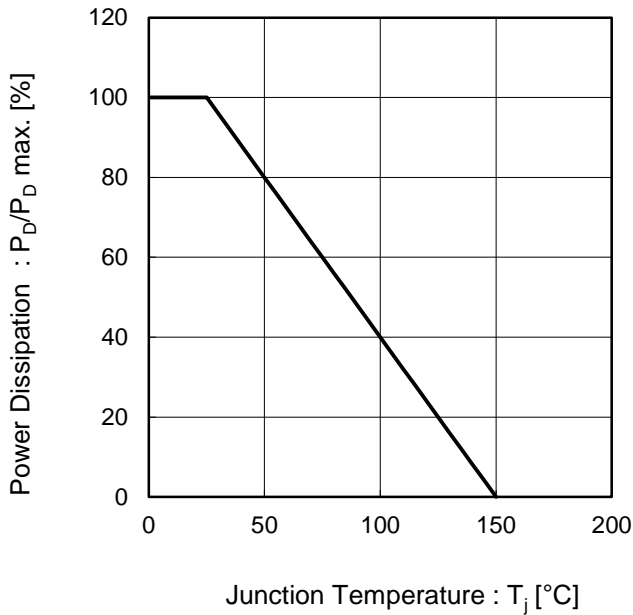


Fig.2 Drain Current Derating Curve

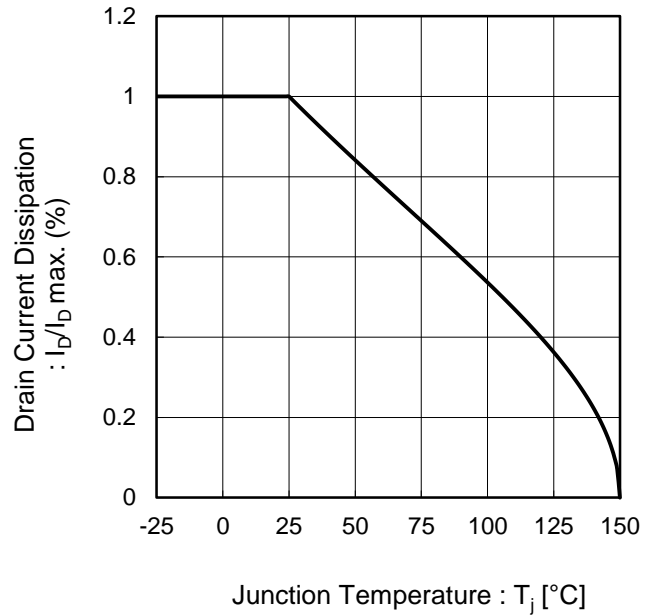


Fig.3 Typical Output Characteristics(I)

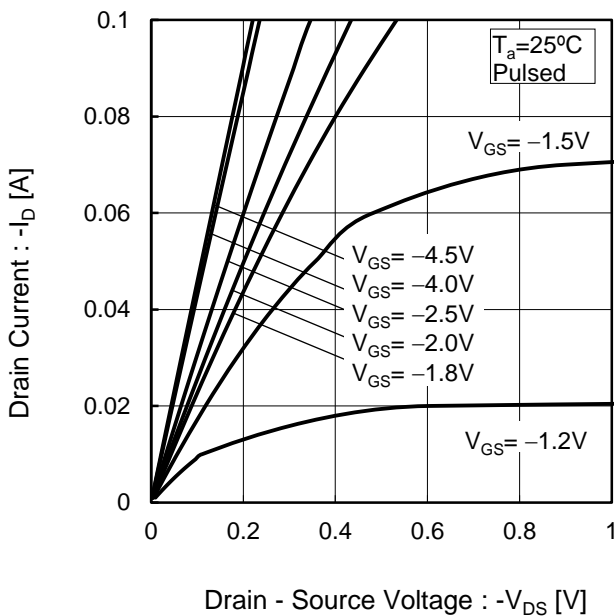
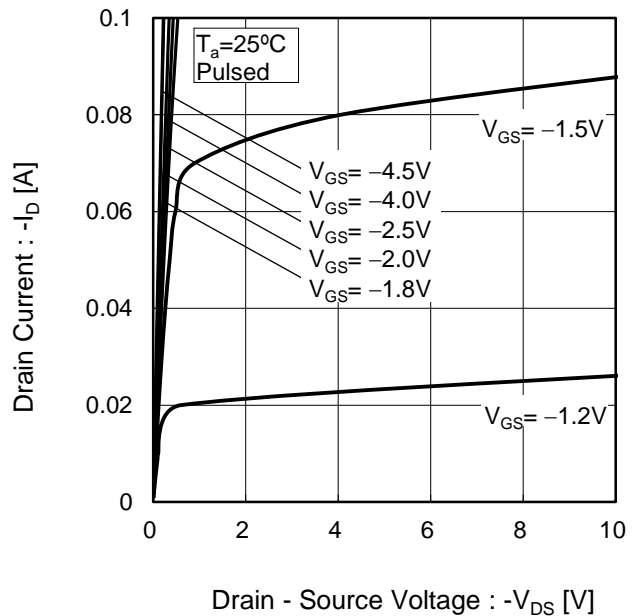


Fig.4 Typical Output Characteristics(II)



●Electrical characteristic curves

Fig.5 Breakdown Voltage vs. Junction Temperature

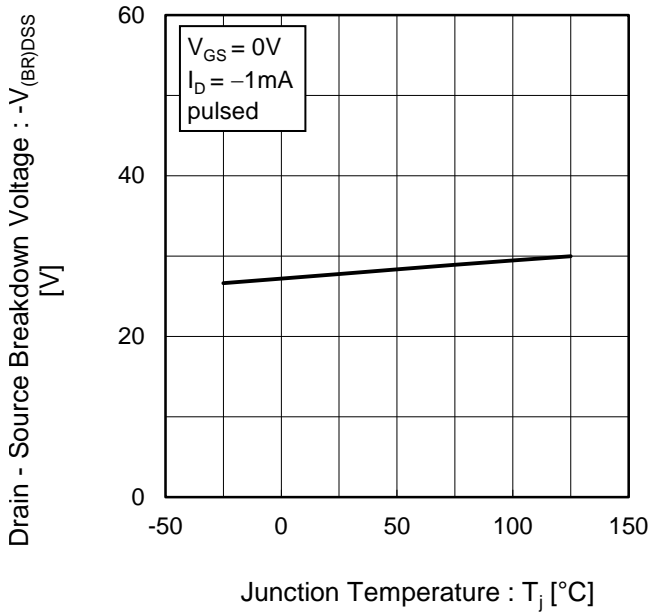


Fig.6 Typical Transfer Characteristics

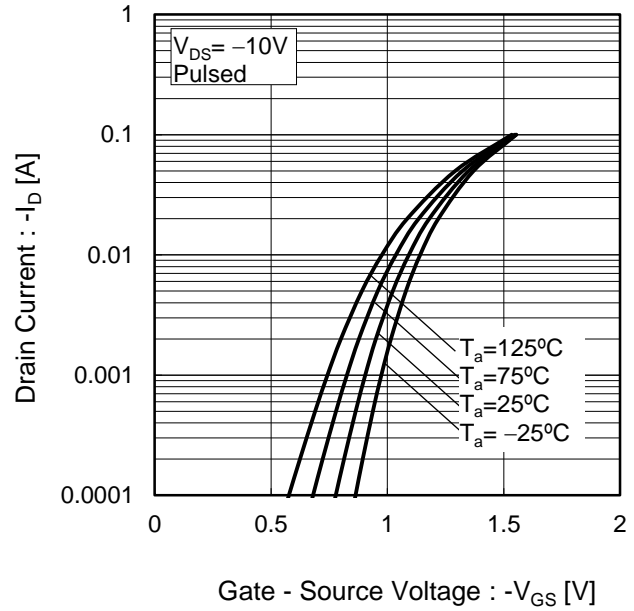


Fig.7 Gate Threshold Voltage vs. Junction Temperature

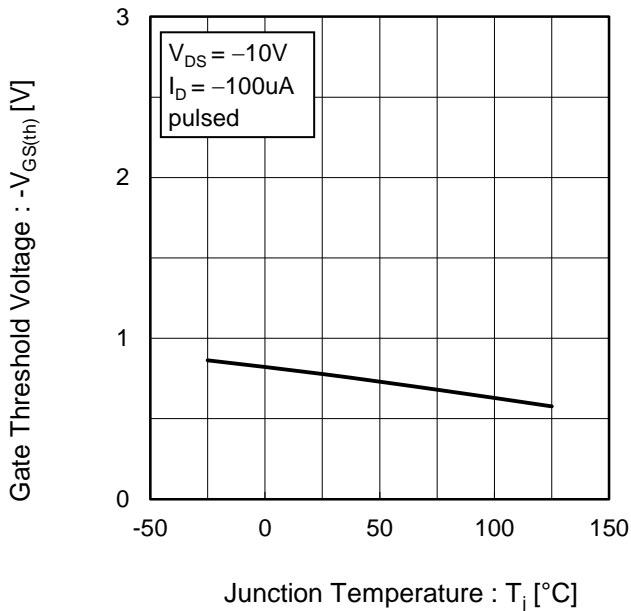
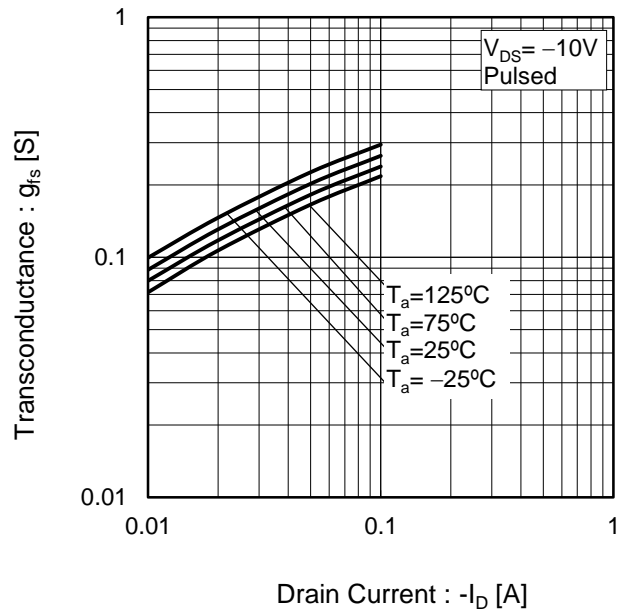


Fig.8 Transconductance vs. Drain Current



●Electrical characteristic curves

Fig.9 Static Drain - Source On - State Resistance vs. Gate Source Voltage

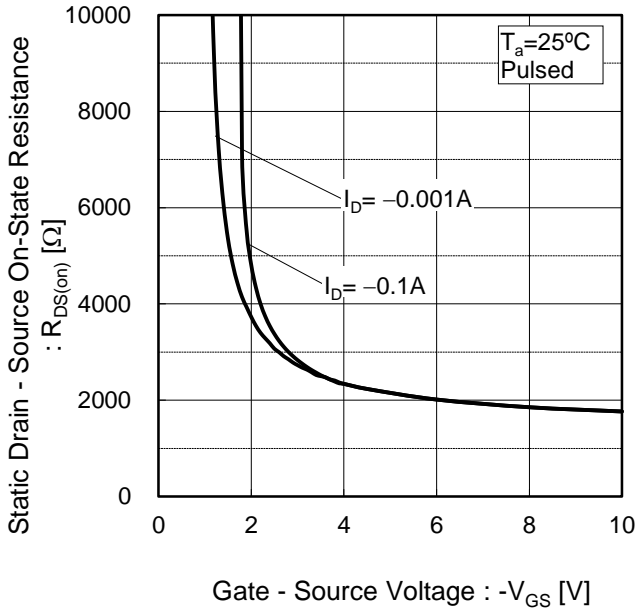


Fig.10 Static Drain - Source On - State Resistance vs. Drain Current(I)

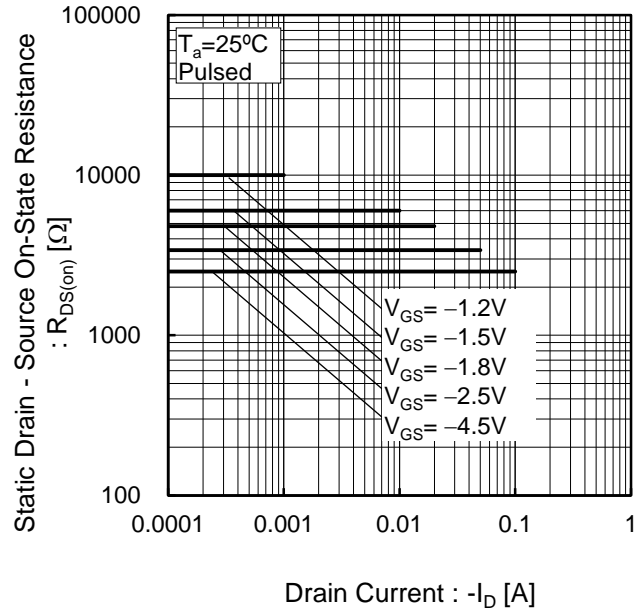


Fig.11 Static Drain - Source On - State Resistance vs. Junction Temperature

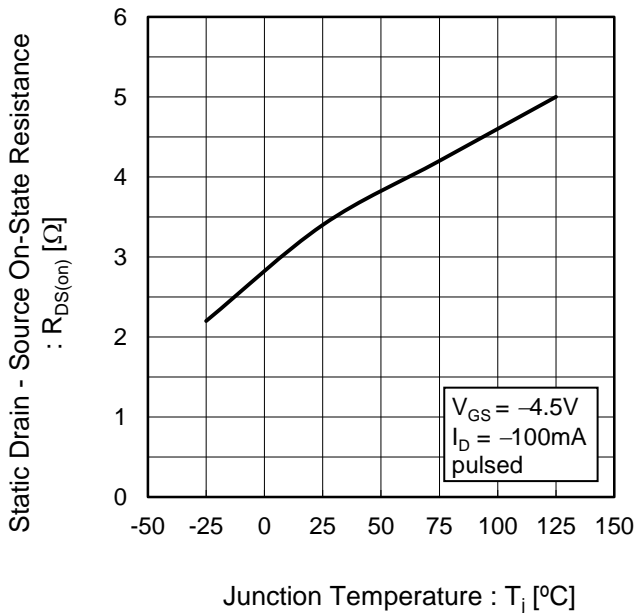
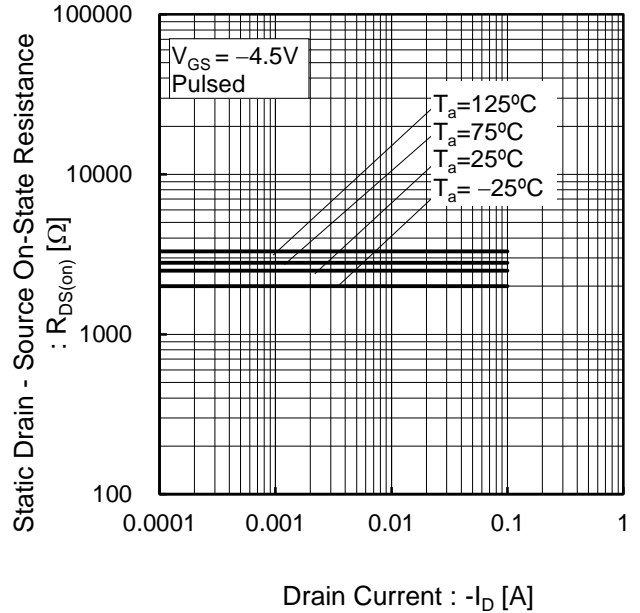


Fig.12 Static Drain - Source On - State Resistance vs. Drain Current(II)



●Electrical characteristic curves

Fig.13 Static Drain-Source On-State Resistance vs. Drain Current(III)

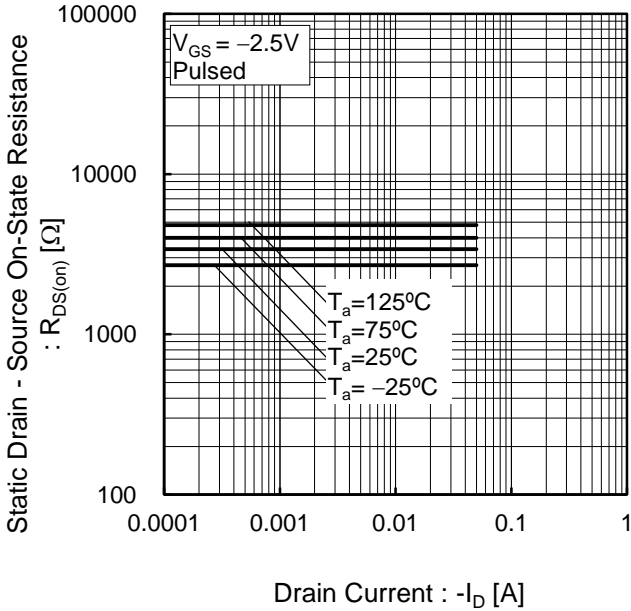


Fig.14 Static Drain - Source On - State Resistance vs. Drain Current(IV)

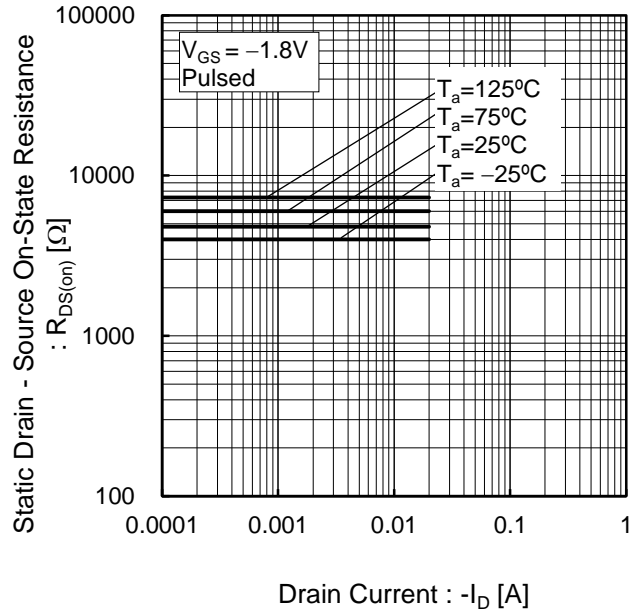


Fig.15 Static Drain - Source On - State Resistance vs. Drain Current(V)

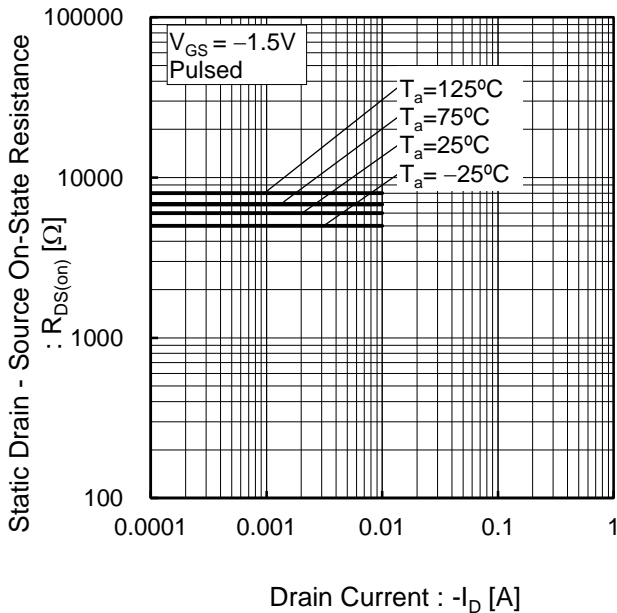
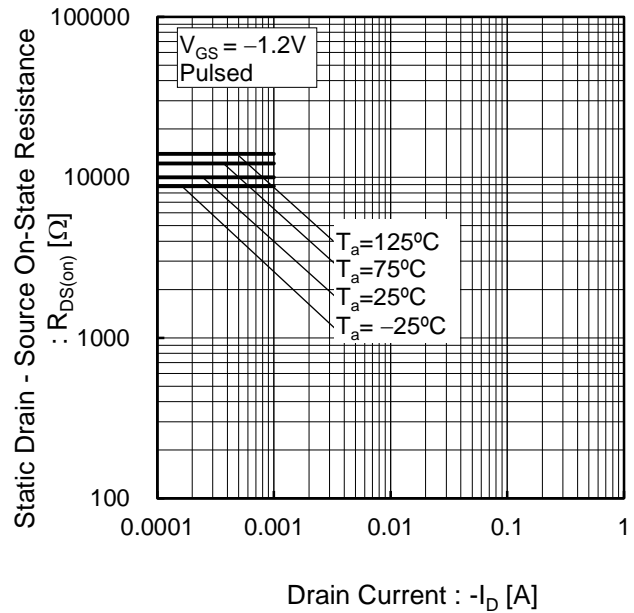


Fig.16 Static Drain - Source On - State Resistance vs. Drain Current(VI)



●Electrical characteristic curves

Fig.17 Typical Capacitance vs. Drain - Source Voltage

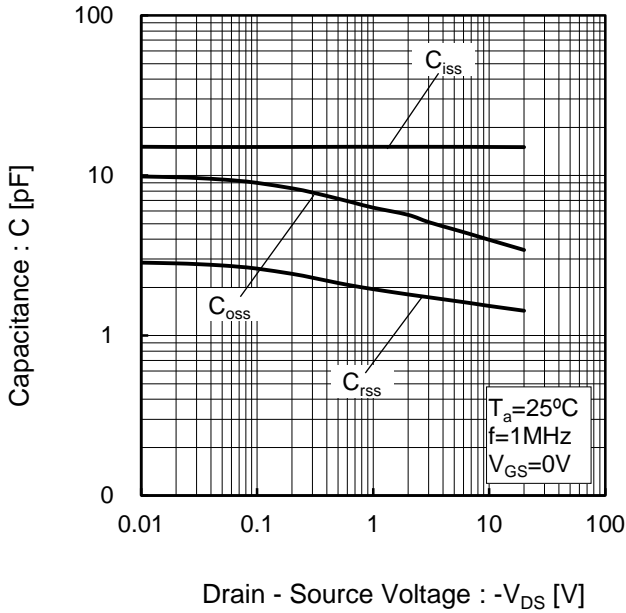


Fig.18 Switching Characteristics

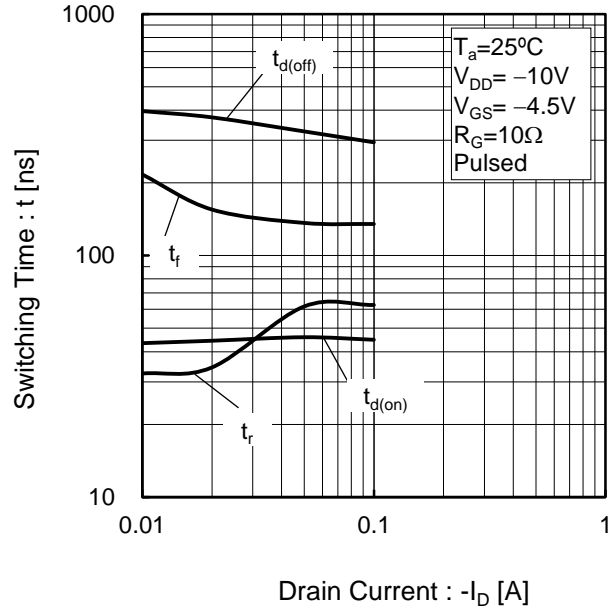
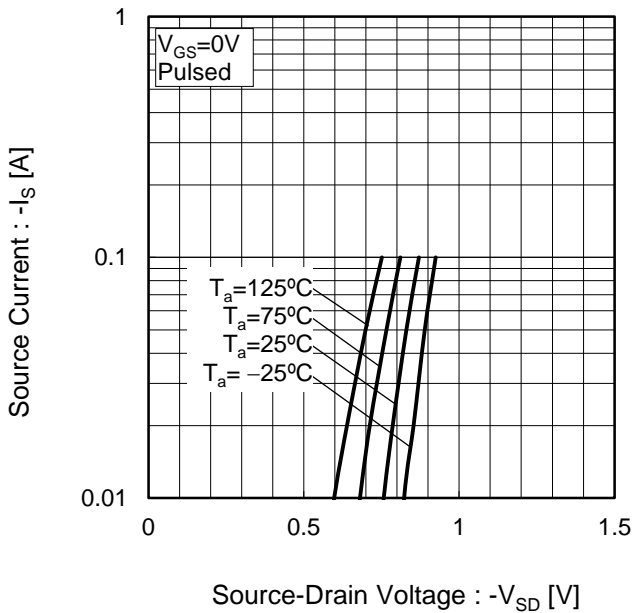


Fig.19 Source Current vs. Source Drain Voltage



●Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

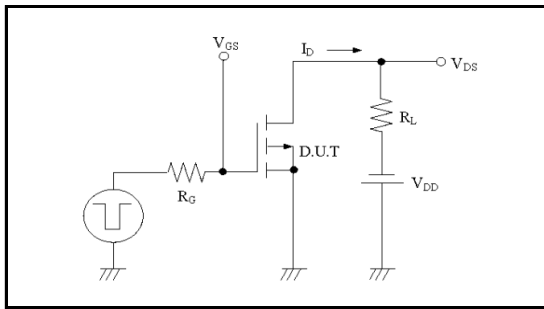
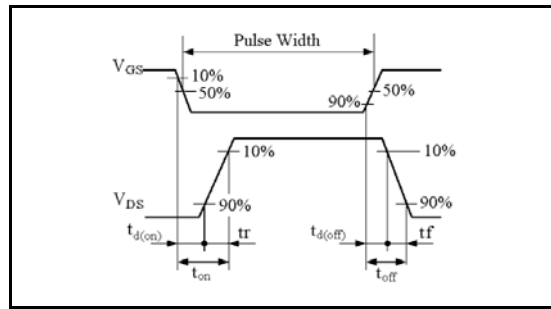


Fig.1-2 Switching Waveforms

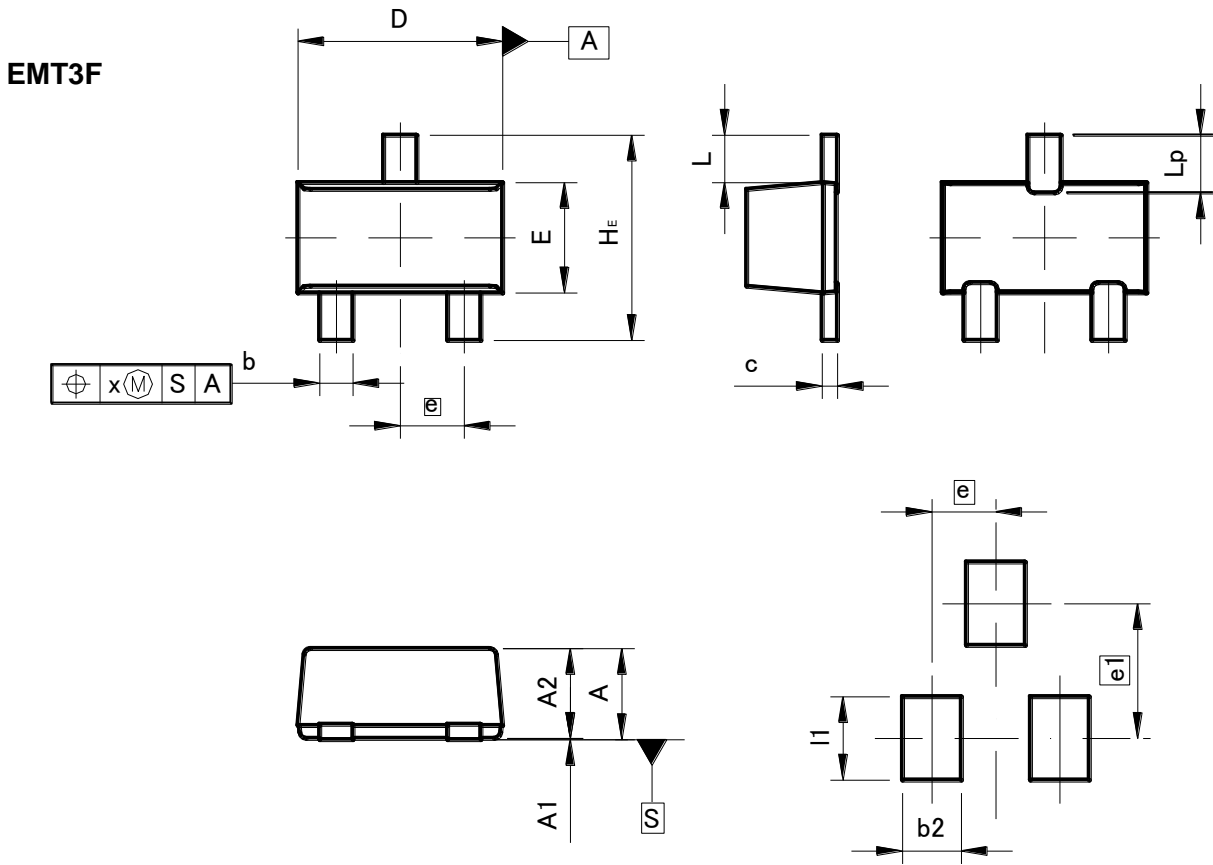


●Notice

This product might cause chip aging and breakdown under the large electrified environment.

Please consider to design ESD protection circuit.

●Dimensions (Unit : mm)



Pattern of terminal position areas

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.65	0.85		
A1	0.00	0.10	0	0.004
A2	0.60	0.80	0.024	0.031
b	0.21	0.36	0.008	0.014
c	0.08	0.18	0.003	0.007
D	1.50	1.70	0.059	0.067
E	0.76	0.96	0.03	0.038
e	0.50		0.02	
HE	1.50	1.70	0.059	0.067
L	0.37		0.015	
Lp	0.35	0.55	0.014	0.022
x	-	0.10	-	0.004

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
e1	-	1.05	-	0.041
b2	-	0.46	-	0.018
l1	-	0.65	-	0.026

Dimension in mm/inches

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